

Question 1 [25 M]

(1) Define the following terms

a- Semiconductors. b- Doping. c- Diffusion current. d- Zener effect.

(2) Draw and explain briefly the structure and operation of P-N junction diode.

(3) Consider a pn junction in equilibrium at $T = 27^\circ\text{C}$ for which the doping concentration are $N_A = 10^{18}/\text{cm}^3$ and $N_D = 10^{16}/\text{cm}^3$ and the cross-sectional area $A = 2 \times 10^{-4}\text{cm}^2$. Where $\epsilon_s = 1.04 \times 10^{-12}\text{F/cm}$, $n_i = 1.5 \times 10^{10}/\text{cm}^3$, $V_T = 25.9\text{mV}$, $q = 1.6 \times 10^{-19}\text{eV}$. Calculate the following:

- Concentration of minority (electrons) in p-region (n_{p0}).
- Concentration of minority (holes) in p-region (p_{n0}).
- Barrier voltage across the junction (v_o).
- The width of the depletion layer (w).
- Width of depletion region in p-region (x_p).
- Width of depletion region in n-region (x_n).
- Total stored charge on either side of depletion region (Q_J)

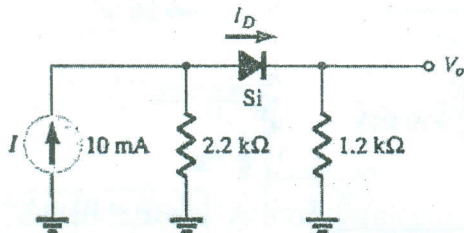
Question 2 [20 M](1) For the circuit shown in Figure 1. Calculate I_D, V_o .(2) For the circuit shown in Figure 2, calculate I_1, I_2, I_{D2} .

Figure 1

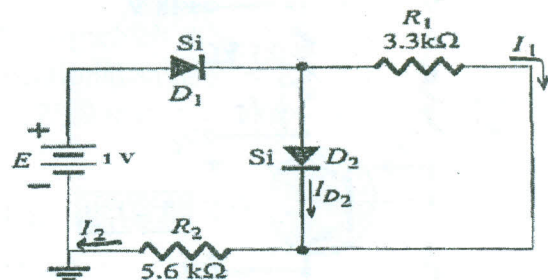


Figure 2

(3) For the circuit shown in Figure 3

- Determine V_L, I_L, I_Z and I_R if $R_L = 180\ \Omega$.
- Repeat (a) if $R_L = 470\ \Omega$.
- Determine the value of R_L that will establish maximum power condition for the zener diode.
- Determine the minimum value of R_L to ensure that the zener diode is in the "on" state.

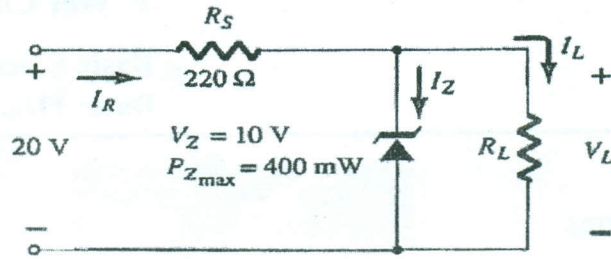


Figure 3

Question 3 [20 M]

- (1) For the circuit shown in Figure 4, draw i_R and v_o for the input v_i .
- (2) Draw v_o for the circuit shown in Figure 5

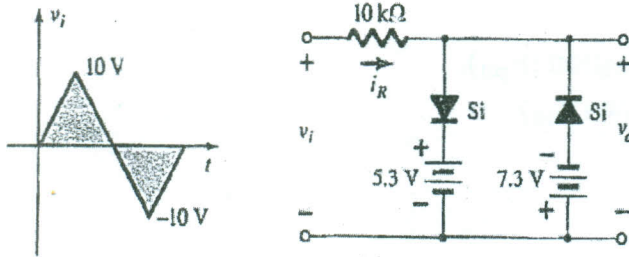


Figure 4

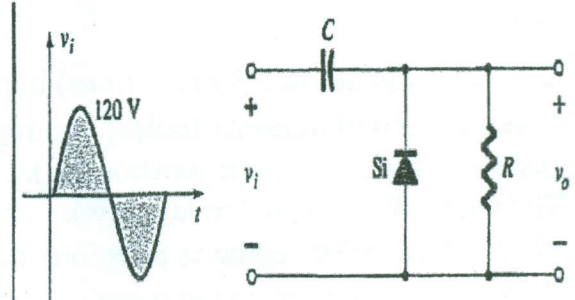


Figure 5

Question 4 [25 M]

- (1) For the BJT circuit shown in Figure 6 determine: I_B, I_C, V_B, V_C, V_E .
- (2) For the FET circuit shown in Figure 7 determine: V_G, I_D, V_G, V_S, V_D .

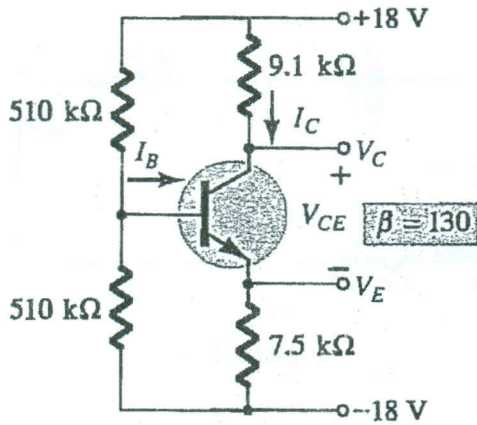


Figure 6

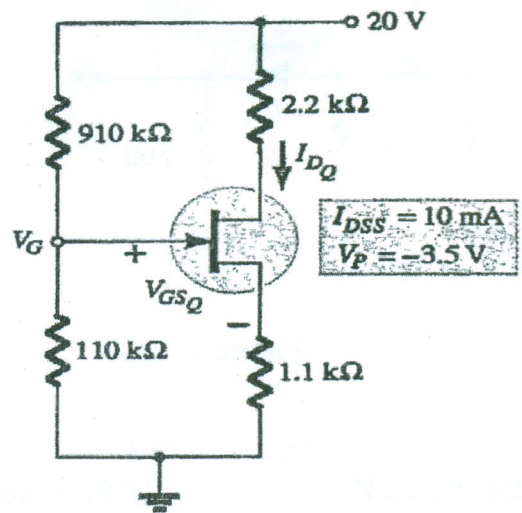


Figure 7